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APPLICANT(S): Shahar Atir  
SERIAL NO.: 10/826,375  
FILED: 04/19/2004  
Page 2**AMENDMENTS TO THE CLAIMS**

Please add or amend the claims to read as follows, and cancel without prejudice or disclaimer to resubmission in a divisional or continuation application claims indicated as cancelled:

1. (currently amended) A method of reading data in a virtual ground array of memory cells comprising: mitigating neighboring effect by sensing substantially simultaneously a state of adjacent memory cells through at least a partially shared sensing path.
2. (original) The method of claim 1, wherein said sensing substantially simultaneously comprises: coupling a sensing circuit to a first source/drain terminal of each cell of said adjacent memory cells; setting a voltage at a second drain/source terminal of each cell of said adjacent cells to a read level; and sensing in a reading direction the state of said adjacent cells.
3. (original) The method according to claim 1, wherein said adjacent cells share at least a word line.
4. (original) The method according to claim 1, wherein said adjacent cells share at least an inside bit line.
5. (original) The method according to claim 2, wherein said coupling a sensing circuit to a first source/drain further comprising coupling said sensing circuit to a shared bit line of said adjacent cells.
6. (original) The method according to claim 2, wherein said coupling a sensing circuit to a first source/drain further comprising coupling said sensing circuit to bit lines of said adjacent cells that are not shared by said adjacent cells.
7. (original) The method according to claim 1, wherein any one of said memory cells stores at least one bit in said charge trapping region.

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8. (original) The method according to claim 1, wherein said adjacent cells are sensed with substantially identical current.

9. (original) The method according to claim 1, wherein said memory cells are nitride read only memory (NROM) cells.

10. (original) The method according to claim 2, wherein said coupling a sensing circuit to a first source/drain further comprising coupling said sensing circuit through select transistors to shared or not shared bit lines.

11. (original) The method according to claim 2, wherein said coupling a sensing circuit to a first source/drain further comprising coupling said sensing circuit substantially directly to not shared bit lines.

12. - 17. (withdrawn)